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Coherent Quantum Ratchets Driven by Tunnel Oscillations

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We demonstrate that the tunnel oscillations of a biased double quantum dot can be employed as driving source for a quantum ratchet. As a model, we use two capacitively coupled double quantum dots. One double dot is voltage biased and provides the ac force, while the other experiences the ac force and acts as coherent quantum ratchet. The current is obtained from a Bloch-Redfield master equation which ensures a proper equilibrium limit. We find that the two-electron states of the coupled ratchet-drive Hamiltonian lead to unexpected steps in the ratchet current.

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The ratchet effect, i.e. the induction of a dc current by an ac force in the absence of any net bias, represents one of the most intriguing phenomena in the field of non-equilibrium transport [1, 2]. Its quantum version [3], has been observed, e.g., in nanostructured two-dimensional electron gases [4], double quantum dots [5], Josephson junctions [6, 7], and Josephson junction arrays [8]. In all these experiments, spatially asymmetric potentials are driven by an external ac field stemming from a *classical* radiation source. By contrast, we here address the question whether the tunnel oscillations of a single electron can be employed to induce a sizable ratchet current.

Recently a quantum ratchet has been realized with a double quantum dot driven by the non-equilibrium noise of a close-by quantum point contact ("drive circuit") [9]. The observed current exhibits characteristic ratchet features such as current reversals and a vanishing current at symmetry points. If the relevant energy levels of the double quantum dot are strongly detuned, the inter-dot tunneling is incoherent and occurs at a rate that can be derived within $P(E)$ theory [10]. The resulting current is proportional to the noise correlation function and, thus, the ratchet can serve as frequency-resolved noise detector [11, 12, 13]. However, when the detuning becomes of the order of the inter-dot coupling, coherent tunnel oscillations emerge and, thus, a treatment beyond $P(E)$ theory becomes necessary.

In the scenario sketched so far, the drive circuit entails a force on the ratchet, while the corresponding backaction is ignored. While this is a valid approach for classical driving fields, it becomes inadequate when the driving force stems from a single quantum mechanical degree of freedom [14, 15]. Therefore, a consistent description requires including the drive circuit into the model. We consider the setup sketched in Fig. 1, where both the ratchet and the drive circuit are formed by double quantum dots that are capacitively coupled. Thereby we find even for small capacitive coupling a sizable ratchet current and, moreover, elucidate the role of eigenstates with one electron in the drive circuit and one in the ratchet.

Capacitively coupled double quantum dots.—The setup of Fig. 1 is described by the Hamiltonian $H = H_{\rm dots} + \sum_\ell V_\ell + \sum_\ell H_\ell$, where

$$H_{\rm dots} = \sum_{\ell=1}^{4} \epsilon_\ell n_\ell - \frac{\Omega}{2}(c_2^\dagger c_1 + c_1^\dagger c_2) - \frac{\Omega_{\rm dr}}{2}(c_4^\dagger c_3 + c_3^\dagger c_4) + U(n_1 n_3 + n_2 n_4) \tag{1}$$

refers to the two double quantum dots. Each of the four dots D_ℓ, $\ell = 1, \ldots, 4$ is treated as a single level $|\ell\rangle$ with onsite energy ϵ_ℓ. The operators $c_\ell^\dagger$ and c_ℓ create and annihilate, respectively, an electron on dot D_ℓ, and $n_\ell = c_\ell^\dagger c_\ell$ is the corresponding number operator. The second and third terms constitute electron tunneling between dots D_1 and D_2 and between D_3 and D_4 with tunnel couplings Ω and $\Omega_{\rm dr}$. The last term describes the capacitive interaction between neighboring dots of opposite circuits. For the present purpose, it is sufficient to consider only up to one spinless electron per double dot.

Each dot D_ℓ is coupled to a lead ℓ fully described by $H_\ell = \sum_q \epsilon_q c_{\ell q}^\dagger c_{\ell q}$ and $\langle c_{\ell q}^\dagger c_{\ell' q'} \rangle = f(\epsilon_q - \mu_\ell)\delta_{\ell\ell'}\delta_{qq'}$ with chemical potential μ_ℓ and the Fermi function $f(x) = [\exp(x/k_BT) + 1]^{-1}$. The dot-lead contact is established

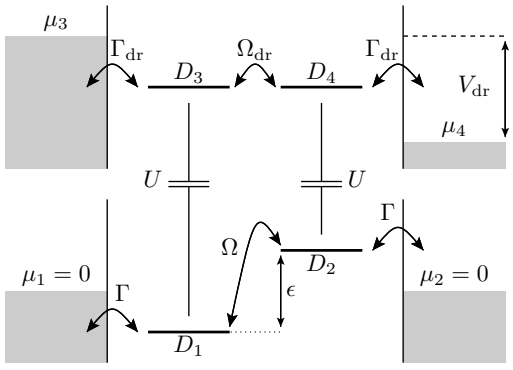

FIG. 1: Capacitively coupled double quantum dots acting as quantum ratchet (dots $D_{1,2}$ with onsite energies $\epsilon_1 = -\epsilon/2$, $\epsilon_2 = \epsilon/2$) and drive circuit (dots $D_{3,4}$ with $\epsilon_3 = \epsilon_4 = 0$), respectively, where each dot is coupled to a lead. The tunnel oscillations in the drive circuit are maintained by a voltage bias, while the ratchet is detuned, but unbiased.

by the tunnel Hamiltonian $V_\ell = \sum_q V_{\ell q} c_{\ell q}^\dagger c_\ell + \text{h.c.}$ We assume within a wide-band limit that all coupling strengths $\Gamma_\ell(\epsilon) = 2\pi \sum_q |V_{\ell q}|^2 \delta(\epsilon - \epsilon_q)$ are energy independent and that the setup is symmetric such that $\Gamma_1 = \Gamma_2 = \Gamma$ and $\Gamma_3 = \Gamma_4 = \Gamma_{\rm dr}$.

By established techniques [16], we derive for the reduced density operator of the dots, ρ, the Bloch-Redfield master equation (in units with $\hbar = 1$)

$$\dot\rho = -i[H_{\rm dots}, \rho] - \text{tr}_{\rm leads} \int_0^\infty d\tau \sum_\ell [V_\ell, [\tilde V_\ell(-\tau), R]], \quad (2)$$

where $R = \rho \otimes \rho_{\rm leads}$. The tilde denotes the interaction picture operator $\tilde x(t) = U_0(t)^\dagger x U_0(t)$ with $U_0(t) = \exp[-i(H_{\rm dots} + \sum_\ell H_\ell)t]$ the propagator in the absence of dot-lead tunneling. The inter-dot tunneling, however, has to be included in U_0 to ensure compliance with equilibrium conditions [17]. This is in the present case of particular importance, because otherwise the master equation would provide a spurious current which may even be larger than the ratchet current. The central quantities of interest are the currents through the dot-lead contacts which we define as the time-derivative of the charge in the respective lead, $I_\ell = -e(d/dt)N_\ell$. After some algebra, we obtain [18] $I_\ell = \text{tr}(\mathcal{J}_\ell^{\rm out} - \mathcal{J}_\ell^{\rm in})\rho$, where

$$\mathcal{J}_\ell^{\rm out}\rho = \frac{e\Gamma_\ell}{2\pi} \int_0^\infty d\tau \int d\epsilon\, e^{-i\epsilon\tau} \tilde c_\ell(-\tau) \rho c_\ell^\dagger f_\ell(\epsilon) + \text{h.c.}, \quad (3)$$

and $\mathcal{J}_\ell^{\rm in}$ is formally obtained from $\mathcal{J}_\ell^{\rm out}$ by the replacement $(c_\ell^\dagger, c_\ell, f_\ell) \to (c_\ell, c_\ell^\dagger, 1 - f_\ell)$.

For the numerical solution of the master equation (2), we need to cope with the interaction picture representation of the tunneling operators V_ℓ. For the lead operators, we readily insert $c_{\ell q}(t) = c_{\ell q} \exp(-i\epsilon_q t)$, while for the dot operators, we accomplish this task by decomposing both the master equation and the current operators into the eigenstates of $H_{\rm dots}$. Thus, we have to solve the eigenvalue equation $H_{\rm dots}|\phi_\alpha^{(n)}\rangle = E_\alpha^{(n)}|\phi_\alpha^{(n)}\rangle$. The complementary index (n) reflects the respective electron number $n \equiv n_\alpha = \langle\phi_\alpha^{(n)}| \sum_\ell n_\ell |\phi_\alpha^{(n)}\rangle$. Then the master equation assumes the form $\dot\rho_{\alpha\beta} = -i[E_\alpha^{(n)} - E_\beta^{(n)}]\rho_{\alpha\beta} + \sum_{\alpha'\beta'} \mathcal{L}_{\alpha\beta,\alpha'\beta'}\rho_{\alpha'\beta'}$. The full expression for $\mathcal{L}_{\alpha\beta,\alpha'\beta'}$ is somewhat lengthy so that we do not write it explicitly.

Stochastic ac driving.—Before addressing the question how the ratchet acts back on the drive circuit, we work out the scenario in which electrons tunneling through the drive circuit entail an effective ac force on the ratchet. In doing so, we generalize the previous $P(E)$ theory treatment [11] to the case of delocalized ratchet electrons.

The effective ac driving can be obtained from Hamiltonian (1) as follows. An electron on dot D_3 shifts the onsite energy ϵ_1 by U, while ϵ_2 is shifted by U if an electron resides on dot D_4, i.e. the ratchet detuning $\epsilon = \epsilon_2 - \epsilon_1$ changes by $U\xi$, where $\xi = n_4 - n_3$. Hence the ratchet acquires the stochastic Hamiltonian

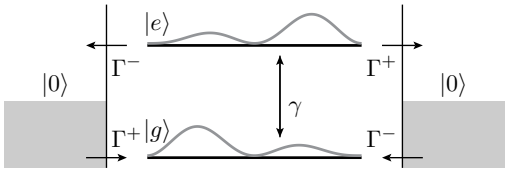

FIG. 2: Transitions between the one-electron states $|g\rangle$, $|e\rangle$ and the empty state $|0\rangle$ of the stochastically ac driven ratchet.

$H_{\rm noise} = \frac{U}{2}\xi(n_2 - n_1)$. For its treatment with Fermi's golden rule, we need to compute the Fourier transformed $\hat C(\omega)$ of the correlation function $C(t) = \langle\xi(t)\xi(0)\rangle$. For large bias voltage $\mu_3 - \mu_4 \gg \Omega_{\rm dr}$, all levels of the drive circuit lie within the voltage window. Then the corresponding Bloch-Redfield equation assumes the Lindblad form $\mathcal{L}_{\rm dr} = -\frac{i}{2}\Omega_{\rm dr}[c_3^\dagger c_4 + c_4^\dagger c_3, \rho] + \Gamma_{\rm dr}\mathcal{D}(c_3^\dagger)\rho + \Gamma_{\rm dr}\mathcal{D}(c_4)\rho$ with the superoperator $\mathcal{D}(x)\rho = x\rho x^\dagger - \frac{1}{2}x^\dagger x\rho - \frac{1}{2}\rho x^\dagger x$. Employing the quantum regression theorem [19], we obtain

$$\hat C(\omega) = \frac{\Gamma_{\rm dr}^2 + 2\Omega_{\rm dr}^2}{\Gamma_{\rm dr}^2 + 3\Omega_{\rm dr}^2} \frac{\Gamma_{\rm dr}/2}{(\omega - \Omega_{\rm dr})^2 + \Gamma_{\rm dr}^2/4} + (\Omega_{\rm dr} \to -\Omega_{\rm dr}), \quad (4)$$

i.e. a double Lorentzian with peaks at $\pm\Omega_{\rm dr}$. In the time domain, $C(t) \propto \cos(\Omega_{\rm dr}t)\exp(-\Gamma_{\rm dr}t/2)$ which underlines the ac character of the stochastic force ξ for $\Gamma_{\rm dr} \ll \Omega_{\rm dr}$.

The Hamiltonian $H_{\rm noise}$ induces transitions between the one-electron eigenstates of the ratchet Hamiltonian, $|g\rangle = \cos\theta|1\rangle + \sin\theta|2\rangle$ and $|e\rangle = -\sin\theta|1\rangle + \cos\theta|2\rangle$ with $\cos(2\theta) = \epsilon/E$ and the level splitting $E = (\epsilon^2 + \Omega^2)^{1/2}$. For sufficiently small U, a golden rule calculation with the transition matrix element $\langle e|H_{\rm noise}|g\rangle = \frac{1}{2}U\xi\sin(2\theta)$ yields the rate $\gamma = \frac{1}{4}U^2\sin^2(2\theta)\hat C(E)$. Once the electron is in the excited state $|e\rangle$, it may tunnel to lead 1 or to lead 2. In turn, if the ratchet double dot is in the empty state $|0\rangle$, an electron may tunnel from one of the leads to the ground state $|g\rangle$. By transforming the current operators $\mathcal{J}_{1,2}^{\rm out/in}$ into the basis $\{|e\rangle, |g\rangle\}$, we find that the transition rates are proportional to the overlaps $|\langle\ell|e\rangle|^2$, $\ell = 1, 2$. Thus we obtain for transitions between the ratchet states the stochastic process sketched in Fig. 2 with the rates $\Gamma^+ = \Gamma\cos^2\theta$ and $\Gamma^- = \Gamma\sin^2\theta$.

It is straightforward [20] to find for the occupation probabilities the master equation

$$\frac{d}{dt}\begin{pmatrix} p_0 \\ p_g \\ p_e \end{pmatrix} = \begin{pmatrix} -\Gamma & 0 & \Gamma \\ \Gamma & -\gamma & \gamma \\ 0 & \gamma & -(\Gamma+\gamma) \end{pmatrix} \begin{pmatrix} p_0 \\ p_g \\ p_e \end{pmatrix}, \quad (5)$$

and the current $I = e(\Gamma^+ p_e - \Gamma^- p_0)$, where $\Gamma = \Gamma^+ + \Gamma^-$. From the stationary solution $(p_0, p_g, p_e) \propto (\gamma, \Gamma + \gamma, \gamma)$ follows $I = e\gamma(\Gamma^+ - \Gamma^-)/(\Gamma^+ + \Gamma^- + 3\gamma)$. We insert the above expressions for γ and $\Gamma^\pm$ and express the mixing angle θ in terms of ϵ and Ω to obtain in the limit $\gamma \ll \Gamma$

the ratchet current

$$I = \frac{eU^2}{4}\frac{\epsilon\Omega^2}{(\epsilon^2+\Omega^2)^{3/2}}\hat{C}\Big(\sqrt{\epsilon^2+\Omega^2}\Big). \qquad (6)$$

Notice that the second factor is beyond $P(E)$ theory and represents the essential difference to Ref. [11]. Its origin is the delocalization of the ratchet eigenstates for $\epsilon \lesssim \Omega$. In the present context, this regime is the most intriguing one, because it contains both the current maximum at $\epsilon \approx \Omega$ and the main current reversal at $\epsilon = 0$.

The analytical result (6) already allows an estimate for the size of the ratchet current. The Lorentzian $\hat{C}$ assumes its maximum $\sim 1/\Gamma_{\rm dr}$ if the ratchet and the drive circuit are in resonance, $E = \Omega_{\rm dr}$. The corresponding condition on the second factor of this expression is $\epsilon = \Omega/\sqrt{2}$, so that the maximal ratchet current is roughly $I_{\rm max} = eU^2/5\Gamma_{\rm dr}$. Interestingly enough, this value depends only on the parameters of the drive circuit and on the coupling strength, but not on the ratchet parameters.

In the experiment of Ref. [9], the dot-lead coupling is 40μeV, while the capacitive coupling U is significantly smaller. Assuming $U = 0.2\mu$eV, we obtain $I_{\rm max} \approx 0.1$pA, i.e. the appreciable value measured for driving with a quantum point contact [9]. Two double quantum dots with similar geometry and similar tunnel couplings but with the much stronger interaction $U = 20\mu$eV have already been realized [21], such that a considerably larger ratchet current should be achievable as well.

Backaction on the drive circuit.—Let us now turn to the treatment of the drive circuit as a quantum system that is affected by the coupling to the ratchet. For this purpose, we compute the currents numerically by solving the master equation (2). Figure 3 demonstrates that for the large drive circuit bias $V_{\rm dr} = 10\Omega/e$, the ratchet current agrees quite well with our prediction (6). In particular, it exhibits a current reversal at $\epsilon = 0$, while the current maximum is obtained for $\epsilon \approx \pm\Omega$, i.e. in the coherent regime. The lack of perfect symmetry is due to the fact that on average, dot D_3 is slightly stronger populated than dot D_4. The drive current (inset of Fig. 3) is influenced by the interaction only close to $V_{\rm dr} \approx \Omega_{\rm dr}/e$. For larger $V_{\rm dr}$, the drive current stays practically constant, so that in the picture of stochastic ac driving, no change of the ratchet current is expected.

In contrast to this expectation, however, e.g. for $V_{\rm dr} = 2\Omega/e$ (Fig. 3), the ratchet current exhibits steps similar to those of Coulomb blockade. The location of these steps is best visible in the differential transconductance $\partial I(\epsilon, V_{\rm dr})/\partial V_{\rm dr}$ shown in Fig. 4(b). They are based on the fact that transitions between states with different electron number require the corresponding energy difference to lie within the voltage window. Thus, we can identify the states that govern the transport yielding a full quantum mechanical picture of the ratchet mechanism. By investigating the location of the steps upon variation of μ_3 and μ_4, we find that they relate to the

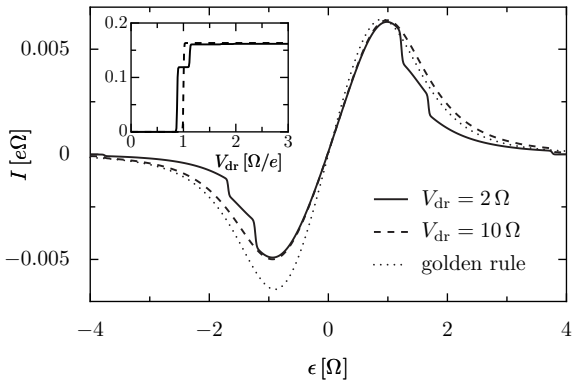

FIG. 3: Ratchet current as a function of the level detuning for various bias voltages at the drive circuit in comparison with the golden-rule result (6). The tunnel couplings are $\Gamma = 0.3\,\Omega$, $\Gamma_{\rm dr} = 0.5\,\Omega$, and $\Omega_{\rm dr} = \Omega$, while the interaction strength is $U = 0.25\,\Omega$. Inset: drive current as a function of $V_{\rm dr}$ for $U = 0$ (dashed) and $U = 0.25\Omega$ (solid), while $\epsilon = 2\Omega$.

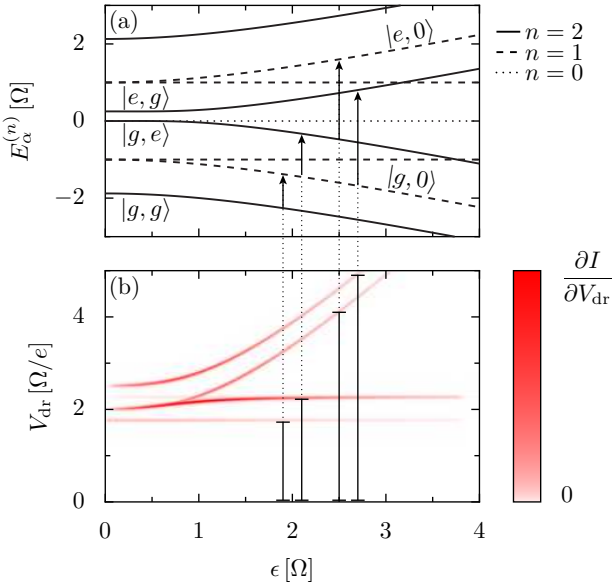

FIG. 4: (a) Eigenenergies of the n-electron states $|\phi_\alpha^{(n)}\rangle$ of the couped double quantum dots for $U = 0.25\,\Omega$. The arrows mark the transitions that govern the ratchet current. (b) Differential transconductance $\partial I/\partial V_{\rm dr}$ highlighting the steps of the ratchet current as a function of the detuning and the bias at the drive circuit. All other parameters are as in Fig. 3.

transitions marked in Fig. 4(a). All relevant transitions involve two-electron states, since the ratchet current is interaction induced.

A more profound discussion of the transport process requires knowledge about the structure of the eigenstates of Hamiltonian (1). For $U = 0$, they are given by the direct products of the ratchet states $|0\rangle$, $|g\rangle$, $|e\rangle$ and the according eigenstates of the drive dots, $|0\rangle_{\rm dr}$, $|g\rangle_{\rm dr}$, and $|e\rangle_{\rm dr}$. Thus, the one-electron states read $|s,0\rangle = |s\rangle|0\rangle_{\rm dr}$ and $|0,s\rangle = |0\rangle|s\rangle_{\rm dr}$, while the two-electron states are

$|s,s'\rangle = |s\rangle|s'\rangle_{\rm dr}$, where $s,s' \in \{g,e\}$. Obviously, the interaction does not affect the one-electron states, while any two-electron state acquires for finite U an admixture of all other two-electron states. From standard perturbation theory follows that the admixture is of the order U^2. For the small values of U considered here, the admixture is small as well and, thus, it is appropriate to keep the notation $|s,s'\rangle$. The consequence of the interaction is that when an electron tunnels from lead 3 via the drive dots to lead 4, the ratchet ground state gains a contribution of the excited ratchet state, i.e. the drive current induces a transition of the type $|g\rangle \to |g\rangle + \lambda|e\rangle$, where $\lambda = \mathcal{O}(U^2)$. Since an excited ratchet electron will leave the dots predominantly towards a particular lead (for $\epsilon > 0$ to lead 2), a ratchet current $I \propto U^2$ will flow.

With this general scenario in mind, it is possible to explain how upon increasing $V_{\rm dr}$, the particular tunnel events come into play. For zero bias voltage, both the ratchet and the drive circuit are at equilibrium in state $|g,g\rangle$. As soon as $\mu_4 = -V_{\rm dr}/2$ drops below the ground state energy of the drive circuit, both a drive current and a tiny ratchet current set in. A second step in the ratchet current is observed when both drive states lie within the voltage window and can be occupied. Only then an electron in the drive circuit performs coherent tunnel oscillations and entail a significant ac force.

The third step relates to the transition $|g,e\rangle \to |e,0\rangle$, i.e. an electron tunneling from the drive dots to lead 4 while transferring approximately the energy ϵ to the ratchet and thereby exciting it. Energy conservation now requires that the drive electron finds in lead 4 an unoccupied state with energy $-\epsilon$, which is the case for $V_{\rm dr} \gtrsim \epsilon$. Shortly after that, tunneling from lead 3 to the drive dot under ratchet excitation, i.e. the transition $|g,0\rangle \to |e,g\rangle$ is enabled as well, causing the forth current step. The latter two tunnel processes have a relatively low probability, so that their influence on the drive current is not noticeable. By contrast, their impact on the ratchet current is significant, because they immediately lead to the directed transport of an ratchet electron. Since this scenario relies on the interaction-induced high-energy components of the drive circuit states, the full ratchet mechanism is active only at unexpectedly large voltages. The underlying formation of two-electron states is not included in the picture of stochastic ac driving and, thus, represents the relevant backaction.

Conclusions.—We have studied a coherent double-dot quantum ratchet similar to that of recent experiments [9, 13], but with a driving stemming from tunnel oscillations in a close-by further double quantum dot. These tunnel oscillations turned out to be sufficiently strong and stable to induce ratchet currents of the order of those in related experiments. A particular feature of our model is that it includes both the ratchet and the drive circuit, which enabled us to go beyond the picture in which the drive circuit is not affected by the ratchet. This revealed that the states of the drive circuit acquire components with high energies, which represents the relevant backaction by the ratchet. The measurable consequences are unexpected steps in the ratchet current. Moreover, our results imply that tunnel oscillations can be employed as on-chip sources of ac driving. Thus we are confident that our results will stimulate further experimental theoretical effort in this direction.

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